

# ABSTRACT OF THE DISCLOSURE

The first present invention provides a nitride based  
 5 semiconductor photo-luminescent device having an active layer having a  
 quantum well structure, the active layer having both at least a high  
 dislocation density region and at least a low dislocation density region  
 lower in dislocation density than the high dislocation density region,  
 wherein the low dislocation density region includes a current injection  
 10 region into which a current is injected, and the active layer is less than  $1 \times 10^{18} \text{ m}^{-3}$  in impurity concentration.